	Hits	Search Text		Time stamp
mber			USPAT;	2003/02/19
IIIDET -	1207	Tamp or "chemical mechanical politiming		14:51
		i hing or higher Milly Of	IBM TDB	
	- 13	nlanarization) and abrasive and pad and	I BIN_I DD	
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	1416	CMP or "chemical mechanical polishing		16:21
	1416		DIO, OLO,	16:21
		and ahrasive and pad and	IBM_TDB	
0		slurry and (alumina or silica or ceria )		
		slurry and (alumina of silica of or		
		and (aluminum or al or titanium or ti or		
1		copper or Cu)	USPAT;	2003/02/19
1	4113	pad with abrasive	EPO; JPO;	16:22
•		1	IBM TDB	
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	000	((CMP or "chemical mechanical polishing"	USPAT;	
5	920	l labing or planarizing of	EPO; JPO;	14:56
	-	planarization) and abrasive and pad and	IBM_TDB	
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	76	///CMP or "chemical mechanical polishing	EPO; JPO;	14:57
6	1	-1: -hima or hianari/illu Ul		
		and abrasive and pad and	IBM_TDB	
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	1	and (aluminum or al or titanium or ti or		
		and (aluminum or al of creating brasive))	İ	1
		copper or Cu) ) and (pad with abrasive))		
	1	and organic and oxidizer	USPAT;	2003/02/19
7	8.0	I/CMP or "chemical mechanical polishing	EPO; JPO;	115:52
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		and ahrasive and pad and	IBM_TDB	£.
		and (alimina or Silica of Certa )	1	Y.
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1	1	copper or Cu) and (benzotral polishing"	1	1
		copper or Cu) and (benzottiazott of zer,	USPAT;	2003/02/19
8	773	copper of (u) and (behavior) (CMP or "chemical mechanical polishing"	EPO; JPO;	16:18
0			IBM TDB	
l		and and and an animal pad and	TDM_TDD	
		1 a lad /alumina or SIIICA OF CELLA /		
		same (aluminum or al or titanium or ti or		
		same (aluminum of al		100/10
		copper or Cu) 6 ((CMP or "chemical mechanical polishing"	USPAT;	2003/02/19
9	51	6 ((CMP or "chemical mechanical political	EPO; JPO;	16:17
10		or polishing or planarizing or	IBM_TDB	
		in the same abrasive and pad and	1	
		- 1 /alumina Or Sill (d Of Cerra /		
		/aluminum or al or titalitum of the		
		. c \ and semiconductor	· ·	2003/02/19
	1	copper or cu) / and Schrister of copper or cu) / and Schrister or cu) / and Schri	USPAT;	
	11	U (CMP OF CHEMICAL MCCHAILTEL F	EPO; JPO;	16:20
1	1	or polishing or planarizing or	IBM_TDB	
		planarization) same abrasive same pad		Ī
		same slurry same (alumina or silica or	T.	
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		1 ti or conner or Cu)	HCDATT.	2003/02/19
	177	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	16:20
11	173	(438/693)).CCLS.	EPO; JPO;	10.20
			IBM_TDB	-002/02/10
1	14	or (((438/690) or (438/691) or (438/692) or	USPAT;	2003/02/19
12	40	$07 \mid (((438/690) \text{ or } (438/691) \text{ or } (438/691)) \text{ or } (438/691) \text{ or } (4$	EPO; JPO;	16:21
		(420/603)) CCTS ) and ((CMP OF CHERICOIT	IBM_TDB	
		langhapidal polishing of polishing of	121122	
		l a minima or planarization) did		
		, in and and sillery alla (atalitia		
	1	or silica or ceria ) and (aluminum or al		
	1	or silica of certa / and (article)		
	1	or titanium or ti or copper or Cu) )	USPAT;	2003/02/19
13	10	1	EPO; JPO;	
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and (nad same attachs same abrasive)	14	44 ((((438/690) or (438/691) or (438/692) or (438/693)).CCLS.) and ((CMP or "chemical mechanical polishing" or polishing or planarizing or planarization) and abrasive and pad and slurry and (alumina or silica or ceria ) and (aluminum or al or titanium or ti or copper or Cu) ) ) and (pad same attach\$ same abrasive)	
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